

## Voltage Output, High or Low Side Measurement, Bi-Directional Zero-Drift Series Current Shunt Monitor

#### **Features**

- Wide common-mode range: -0.3 V to 26 V
- Offset voltage: 150 μV (Max)
  (Enable shunt drops of 10 mV full-scale)
- Accuracy
  - ±1.5% Gain error (Max over temperature)
  - 0.5 μV/°C Offset drift (Typ)
  - 10 ppm/°C Gain drift (Max)
- Choice of Gains:

DIO2399A: 50 V/VDIO2399B: 100 V/V

Quiescent current: 100 μA (Max)

• Packages: SC70-6, thin QFN1.8\*1.4-10

## **Applications**

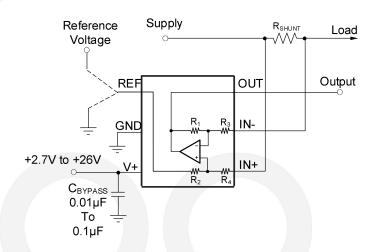
- Notebook computers
- Cell phones
- Telecom equipment
- Power management
- Battery chargers
- Welding equipment

## **Descriptions**

The DIO2399x series of voltage output current shunt monitors can sense drops across shunts at common-mode voltages from -0.3 V to 26 V, independent of the supply voltage. Two fixed gains are available: 50 V/V and 100 V/V. The low offset of the zero-drift architecture enables current sensing with maximum drops across the shunt as low as 10 mV full-scale.

These devices operate from a single 2.7 V to 26 V power supply, drawing a maximum of 100  $\mu$ A of supply current. All versions are specified from -40°C to +105°C, and offered in both SC70-6 and thin QFN1.8\*1.4-10 packages.

## **Block Diagram**



## **Ordering Information**

Part Number	Top Marking	RoHS	TA	Package		
DIO2399ASC6	YW9A	Green	-40 to 105°C	SC70-6	Tape & Reel, 3000	
DIO2399BSC6	YW9B	Green	-40 to 105°C	SC70-6	Tape & Reel, 3000	
DIO2399ALP10	YW9A	Green	-40 to 105°C	QFN1.8*1.4-10	Tape & Reel, 3000	
DIO2399BLP10	YW9B	Green	-40 to 105°C	QFN1.8*1.4-10	Tape & Reel, 3000	



## **Pin Assignments**

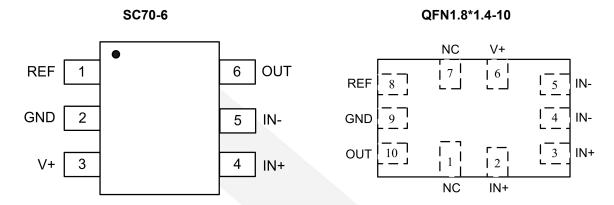


Figure 1. Pin assignment (Top view)

## **Pin Description**

Pin name	Description	
REF	Reference voltage	
GND	Ground	
V+	Positive supply	
IN+	Positive Input	
IN-	Negative Input	
OUT Output		
NC	No connection	



## **Absolute Maximum Ratings**

Stresses beyond those listed under "Absolute Maximum Rating" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other condition beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maxim rating conditions for extended periods may affect device reliability.

	Parameter	Rating	Unit
Supply voltage		+26	V
Analogy inputs V	Differential (V <sub>IN+</sub> ) – (V <sub>IN-</sub> )	-26 to +26	V
Analogy inputs, V <sub>IN+</sub> , V <sub>IN-</sub>	Common-mode	GND-0.3 to +26	V
REF input		GND-0.3 to (V+)+0.3	V
Output		GND-0.3 to (V+)+0.3	V
Input current into all pins		5	mA
Operating temperature		-40 to 105	°C
Storage temperature		-65 to 150	°C
Junction temperature		150	°C
The state of the s	SC70-6	250	°C/W
Thermal resistance θ <sub>JA</sub>	QFN1.8*1.4-10	80	°C/W
ESD	НВМ	±3000	V

## **Electrical Characteristics**

Typical value:  $T_A = 25$ °C,  $V_S = 5$  V,  $V_{IN+} = 12$  V,  $V_{SENSE} = V_{IN+} - V_{IN-}$ , and  $V_{REF} = V_S / 2$ , unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
nput						
$V_{\text{CM}}$	Common-mode input range		-0.3		26	V
CMR	Common-mode rejection	V <sub>IN+</sub> = 0 V to 26 V, V <sub>SENSE</sub> = 0 mV		90		dB
Vos	Offset voltage, RTI	V <sub>SENSE</sub> = 0 mV, V <sub>CM</sub> = V <sub>S</sub> /2		±5	±30	μV
		V <sub>SENSE</sub> = 0 mV, V <sub>CM</sub> = 8 V		±5	±150	μV
dV <sub>OS</sub> /dT	Input vs. Temperature			0.5		μV/°C
PSR	Input vs. Power supply	$V_S = 2.7 \text{ V to } 18 \text{ V}, V_{IN+} = 18 \text{ V}, V_{SENSE} = 0 \text{ mV}$		120		dB
$I_{B}$	Input bias current	V <sub>SENSE</sub> = 0 mV		28		μΑ
Ios	Input offset current	V <sub>SENSE</sub> = 0 mV		±0.02		μA
utput						
G		DIO2399A		50		1/0/
	Gain	DIO2399B	100			- V/V



		<u> </u>						
	Gain error	V <sub>SENSE</sub> = -8 mV to 8 mV		±0.03	±1.5	%		
Voltage output	Voltage output							
	2 : 4 )/.			(V+)	(V+)			
	Swing to V+ power-supply rail	$R_L = 10 \text{ k}\Omega \text{ to GND}$		-	-	V		
				0.05	0.2			
				(V <sub>GND</sub> )	(V <sub>GND</sub> )			
	Swing to GND	$R_L = 10 \text{ k}\Omega \text{ to GND}$		+	+	V		
				0.005	0.05			
Frequency resp	Frequency response							
BW	f (-3 dB) bandwidth	C <sub>LOAD</sub> = 10 pF, DIO2399A		5		kHz		
		C <sub>LOAD</sub> = 10 pF, DIO2399B		5		<u>Κ</u> ΓΙΖ		
SR	Slew rate			0.007		V/µs		
Power supply	Power supply							
Vs	Operating voltage range		2.7		26	V		
1-	Ovices and average	V <sub>SENSE</sub> = 0 mV		65	100	μA		
ΙQ	Quiescent current	Over temperature <sup>(3)</sup>			125	μΑ		

#### Notes:

- (1) RTI = Referred-to-input
- (2) Specifications subject to change without notice.
- (3) Guaranteed by design.



## **Typical Performance Characteristics**

Typical value: T<sub>A</sub> = 25°C, V<sub>S</sub> = 5 V, V<sub>IN+</sub> = 12 V, V<sub>SENSE</sub> = V<sub>IN+</sub> - V<sub>IN-</sub>, and V<sub>REF</sub> = V<sub>S</sub> / 2, unless otherwise specified.

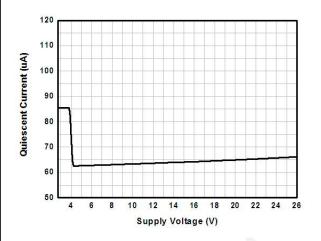


Figure 2. Quiescent current vs. Supply voltage

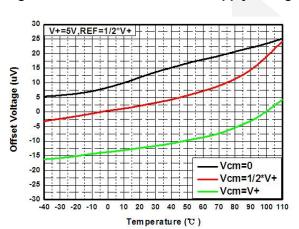


Figure 4. Offset voltage vs. Temperature (DIO2399A: 50V/V)

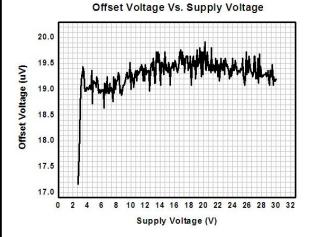


Figure 6. Offset voltage vs. Supply voltage

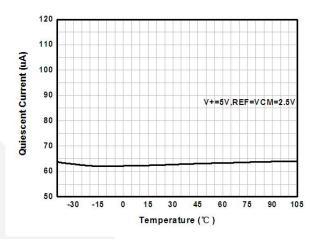


Figure 3. Quiescent current vs. Temperature

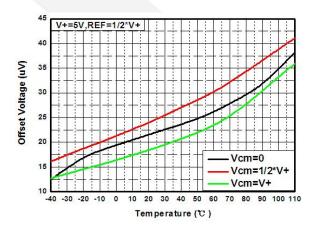


Figure 5. Offset voltage vs. Temperature (DIO2399B: 100V/V)



## **Typical Application**

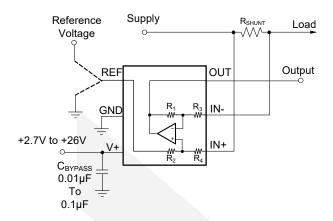


Figure 7. Input and output AC-coupling application

Figure 7 shows the basic connections for the DIO2399x. The input pins, IN+ and IN-, should be connected as closely as possible to the shunt resistor to minimize any resistance in series with the shunt resistance.

Power-supply bypass capacitors are required for stability. Applications with noisy or high-impedance power supplies may require additional decoupling capacitors to reject power-supply noise. Connect bypass capacitors close to the device pins.

On the QFN1.8\*1.4-10 package, two pins are provided for each input. These pins should be tied together (that is, tie IN+ to IN+ and tie IN- to IN-).

#### **Power Supply**

The input circuitry of the DIO2399x can accurately measure beyond its power-supply voltage, V+. For example, the V+ power supply can be 5 V, whereas the load power-supply voltage can be as high as 26 V. However, the output voltage range of the OUT terminal is limited by the voltages on the power-supply pin.

#### Selecting Rs

The zero-drift offset performance of the DIO2399x offers several benefits. Most often, the primary advantage of the low offset characteristic enables lower full-scale drops across the shunt. For example, non-zero-drift current shunt monitors typically require a full-scale range of 100 mV.

The DIO2399x series of current-shunt monitors give equivalent accuracy at a full-scale range on the order of 10 mV. This accuracy reduces shunt dissipation by an order of magnitude with many additional benefits.

Alternatively, there are applications that must measure current over a wide dynamic range that can take advantage of the low offset on the low end of the measurement. Most often, these applications can use the lower gain of 100 to accommodate larger shunt drops on the upper end of the scale.

#### **Unidirectional Operation**

Unidirectional operation allows the DIO2399x to measure currents through a resistive shunt in one direction. The most frequent case of unidirectional operation sets the output at ground by connecting the REF pin to ground. In unidirectional applications where the highest possible accuracy is desirable at very low inputs, bias the REF pin to a convenient value above 50 mV to get the device output swing into the linear range for zero inputs.

A less frequent case of unipolar output biasing is to bias the output by connecting the REF pin to the supply; in this case, the quiescent output for zero input is at quiescent supply. This configuration would only respond to negative currents (inverted voltage polarity at the device input).



#### **Bidirectional Operation**

Bidirectional operation allows the DIO2399x to measure currents through a resistive shunt in two directions. In this case, the output can be set anywhere within the limits of what the reference inputs allow (that is, between 0 V to V+). Typically, it is set at half-scale for equal range in both directions. In some cases, however, it is set at a voltage other than half-scale when the bidirectional current is nonsymmetrical.

The quiescent output voltage is set by applying voltage to the reference input. Under zero differential input conditions the output assumes the same voltage that is applied to the reference input.

#### Input Filtering

An obvious and straightforward filtering location is at the device output. However, this location negates the advantage of the low output impedance of the internal buffer. The only other filtering option is at the device input pins. This location, though, does require consideration of the ±30% tolerance of the internal resistances. Figure 8 shows a filter placed at the inputs pins.

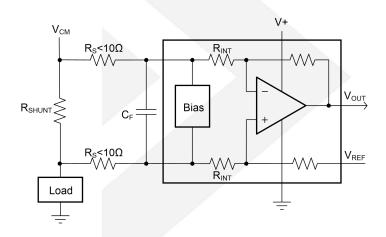


Figure 8. Filter at input pins

The addition of external series resistance, however, creates an additional error in the measurement so the value of these series resistors should be kept to  $10~\Omega$  or less if possible to reduce impact to accuracy. The internal bias network shown in Figure 8 present at the input pins creates a mismatch in input bias currents when a differential voltage is applied between the input pins. If additional external series filter resistors are added to the circuit, the mismatch in bias currents results in a mismatch of voltage drops across the filter resistors. This mismatch creates a differential error voltage that subtracts from the voltage developed at the shunt resistor. This error results in a voltage at the device input pins that is different than the voltage developed across the shunt resistor. Without the additional series resistance, the mismatch in input bias currents has little effect on device operation. The amount of error these external filter resistor add to the measurement can be calculated using Equation 2 where the gain error factor is calculated using Equation 1.

The amount of variance in the differential voltage present at the device input relative to the voltage developed at the shunt resistor is based both on the external series resistance value as well as the internal input resistors, R3 and R4 (or R<sub>INT</sub> as shown in Figure 8). The reduction of the shunt voltage reaching the device input pins appears as a gain error when comparing the output voltage relative to the voltage across the shunt resistor. A factor can be calculated to determine the amount of gain error that is introduced by the addition of external series resistance. The equation used to calculate the expected deviation from the shunt voltage to what is seen at the device input pins is given in Equation 1:

Gain error 
$$Factor = \frac{(1250 \times RINT)}{(1250 \times RS) + (1250 \times RINT) + (RS \times RINT)}$$
(1)



Where:

R<sub>INT</sub> is the internal input resistor (R3 and R4), and

Rs is the external series resistance.

With the adjustment factor equation including the device internal input resistance, this factor varies with each gain version, as shown in Table 1. Each individual device gain error factor is shown in Table 2.

**Table 1. Input Resistance** 

Product	Gain	RINT(kΩ)
DIO2399A	50	20
DIO2399B	100	10

**Table 2. Device Gain Error Factor** 

Product	Simplified Gain Error Factor
DIO2399A	$\frac{20,000}{(17 \times Rs) + 20,000}$
DIO2399B	10,000 (9×Rs)+10,000

The gain error that can be expected from the addition of the external series resistors can then be calculated based on Equation 2:

Gain error(%) = 
$$100-(100*Gain Error Factor)$$
 (2)

#### **REF Input Impedance Effects**

As with any difference amplifier, the DIO2399x series common-mode rejection ratio is affected by any impedance present at the REF input. This concern is not a problem when the REF pin is connected directly to most references or power supplies. When using resistive dividers from the power supply or a reference voltage, the REF pin should be buffered by an op amp.

In systems where the DIO2399x output can be sensed differentially, such as by a differential input analog-to-digital converter (ADC) or by using two separate ADC inputs, the effects of external impedance on the REF input can be cancelled. Figure 9 depicts a method of taking the output from the DIO2399x by using the REF pin as a reference.



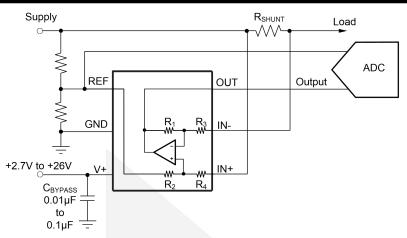


Figure 9. Sensing DIO2399x to cancel effects of impedance on the REF input

#### Using the DIO2399x with common-mode transients above 26 V

With a small amount of additional circuitry, the DIO2399x series can be used in circuits subject to transients higher than 26 V, such as automotive applications. Use only zener diode or zener-type transient absorbers (sometimes referred to as Transzorbs); any other type of transient absorber has an unacceptable time delay. Start by adding a pair of resistors as shown in Figure 10 as a working impedance for the zener. It is desirable to keep these resistors as small as possible, most often around 10  $\Omega$ . Larger values can be used with an effect on gain that is discussed in the section on input filtering. Because this circuit limits only short-term transients, many applications are satisfied with a 10  $\Omega$  resistor along with conventional zener diodes of the lowest power rating that can be found. This combination uses the least amount of board space.

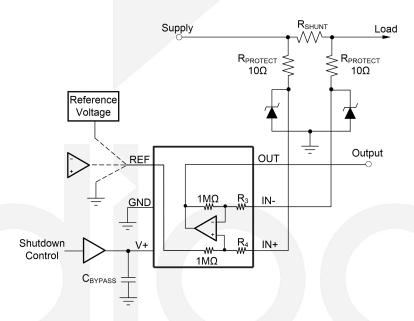


Figure 10. DIO2399x transient protection using dual zener diodes

In the event that low-power zeners do not have sufficient transient absorption capability and a higher power transzorb must be used, the most package-efficient solution then involves using a single transzorb and back-to-back diodes between the device inputs. This method is shown in Figure 11.



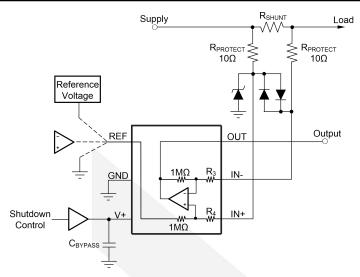


Figure 11. DIO2399x transient protection using a single transzorb and input clamps

#### Improving transient robustness

Applications involving large input transients with excessive dV/dt above 2 kV per microsecond present at the device input pins may cause damage to the internal ESD structures on version A devices. This potential damage is a result of the internal latching of the ESD structure to ground when this transient occurs at the input. With significant current available in most current-sensing applications, the large current flowing through the input transient-triggered, ground-shorted ESD structure quickly results in damage to the silicon. External filtering can be used to attenuate the transient signal prior to reaching the inputs to avoid the latching condition. Care must be taken to ensure that external series input resistance does not significantly impact gain error accuracy. For accuracy purposes, these resistances should be kept under 10  $\Omega$  if possible. Ferrite beads are recommended for this filter because of their inherently low dc ohmic value. Ferrite beads with less than 10  $\Omega$  of resistance at dc and over 600  $\Omega$  of resistance at 100 MHz to 200 MHz are recommended. The recommended capacitor values for this filter are between 0.01  $\mu$ F and 0.1  $\mu$ F to ensure adequate attenuation in the high-frequency region. This protection scheme is shown in Figure 12. (Note: Capacitors used in high voltage applications should be greater than or equal to 30 V)

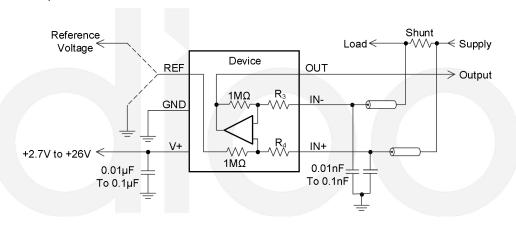
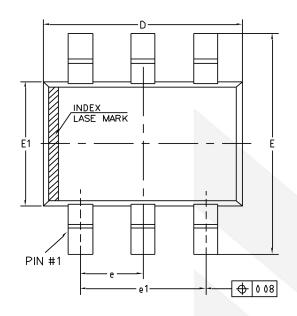


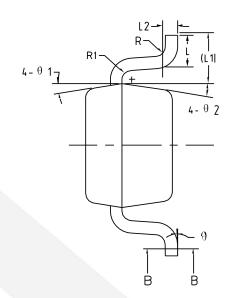
Figure 12. Transient protection

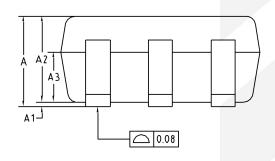
To minimize the cost of adding these external components to protect the device in applications where large transient signals may be present, version B devices are now available with new ESD structures that are not susceptible to this latching condition. Version B devices are incapable of sustaining these damage causing latched conditions so they do not have the same sensitivity to the transients that the version A devices have, thus making the version B devices a better fit for these applications.

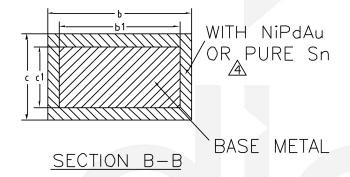
# dioo

## **Physical Dimensions: SC70-6**





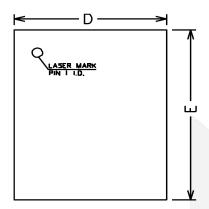




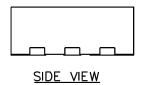
Common Dimensions (Units of measure = Millimeter)					
Symbol	Min	Nom	Max		
Α	0.85	-	1.05		
A1	0	-	0.10		
A2	0.80	0.90	1.00		
A3	0.47	0.52	0.57		
b	0.22	-	0.29		
b1	0.22	0.25	0.28		
С	0.115	-	0.15		
c1	0.115	0.13	0.14		
D	2.02	2.07	2.12		
E	2.20	2.30	2.40		
E1	1.25	1.30	1.35		
е		0.65 BSC			
e1		1.30 BSC			
L	0.28	0.33	0.38		
L1		0.50 REF			
L2		0.15 BSC			
R	0.10	- ,			
R1	0.10	-	0.25		
Θ	0°		8°		
Θ1	6°	9°	12°		
Θ2	6°	9°	12°		

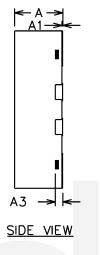


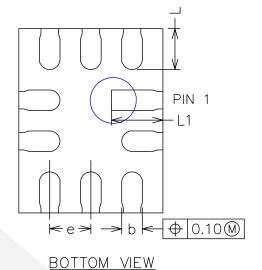
## Physical Dimensions: QFN1.8\*1.4-10



TOP VIEW







Two options



Common Dimensions					
(Units of	(Units of Measure = Millimeter)				
Symbol	Min	Min Nom M			
Α	0.50	0.55	0.60		
A1	0.00	0.02	0.05		
A3	0.152 REF				
b	0.15	0.20	0.25		
D	1.30	1.40	1.50		
E	1.70	1.80	1.90		
е	0.30	0.40	0.50		
L	0.35	0.40	0.45		
L1	0.45	0.50	0.55		



## **CONTACT US**

**D**ioo is a professional design and sales corporation for high-quality and performance analog semiconductors. The company focuses on industry markets, such as, cell phone, handheld products, laptop, and medical equipment and so on. Dioo's product families include analog signal processing and amplifying, LED drivers and charger IC. Go to <a href="http://www.dioo.com">http://www.dioo.com</a> for a complete list of Dioo product families.

For additional product information, or full datasheet, please contact with our Sales Department or Representatives.